Snap-off Diodes (See Outline Drawing No. 37)

Type	Power Dissipation 25°C mw	Peak Surge Current 1 μs amperes	MINIMUM Breakdown Voltage I_R=5μamps B_V Volts	MAXIMUM Capacitance V_R=0V, f=1 mc C_o pf	MINIMUM Stored Charge Q_f pc/ma	TYP. Snap-off time T_S=2 nsec. I_F=20 ma t_{sp} nsec.	MAX.	TYP. Snap-off time T_S=2 nsec. I_F=100 ma tsp nsec.	MAX.
SSA-550(2)/554(3)	250	2	12	1.5	20	0.3	0.5		
SSA-551(2)/555(3)	250	2	8	4.0	20	0.3	0.5		
SSA-552(2)/556(3)	250	2	12	1.5	1.0			0.2(1)	0.4
SSA-553(2)/557(3)	250	2	8	4.0	1.0			0.2(1)	0.4

NOTES: (1) Limited by resolution time of test equipment. (2) DO-7 package. (3) Micro Silicon Diode—see Specifications 75. 28 for outline dimensions.

Microphoto Diodes*(1) — NPN (See Outline Drawing No. 45)

Type	MAX.(2) Bias Volts	MAX.(2) P_C mw	MAX. DARK CURRENT at 24 vdc μa	TYPICAL DARK CURRENT at 24 vdc μa	TYPICAL SENSITIVITY(3, 4) at 250 ft. —c. μa/ft. —c.	at 1000 ft. —c. μa/ft. —c.	TYPICAL PHOTOCURRENT DECAY TIMER μsec.
31F2	40	50	0.1	0.02	0.2	0.8	1
32F2	40	50	0.1	0.02	0.5	1.5	1
33F2	40	50	0.1	0.02	0.9	2.2	1
34F2	40	50	0.1	0.02	1.6	5.0	1

NOTES: *Made in France for General Electric by the Societe Europeenne Des Semiconducteurs (SESCO).
(1) All specs at 25°C unless noted otherwise.
(2) Storage temperature on all types is −65 to +125°C. Operating temperature on all types is −65 to +100°C.
(3) Light source—Tungsten Filament Lamp Operated at a Color Temperature of 2870°K.
(4) Maximum Sensitivity wave length 0.9 to 1.0 microns.